

Microwave Coupling into a Generic Object. FDTD Simulations and Comparison with Measurements.

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Introduction (I)

- Ongoing dispute over the correlation between measurement and simulation
- Discrepancies often seen for complex structures
- Traditional explanation is: “Simulations are wrong and of no use!”
- Our objective: Show that good agreement is indeed achievable by carefully controlling measurements and using high spatial resolution in simulations

Introduction (II)

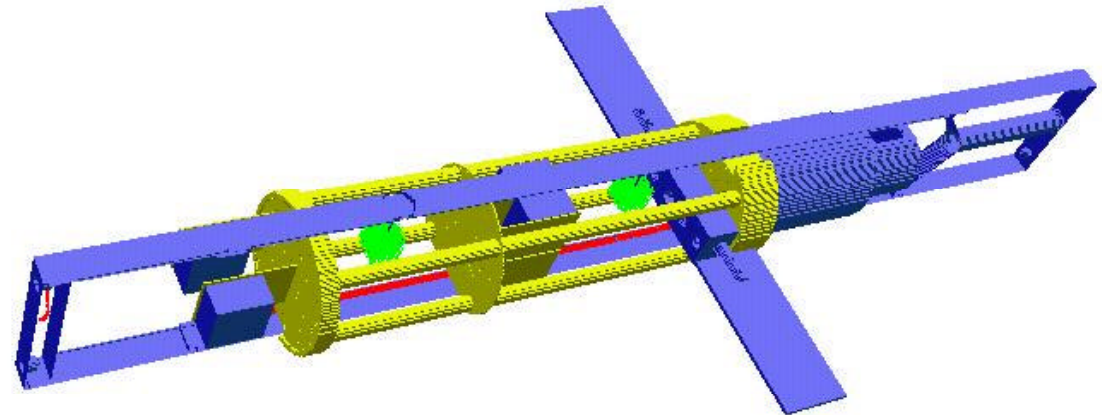
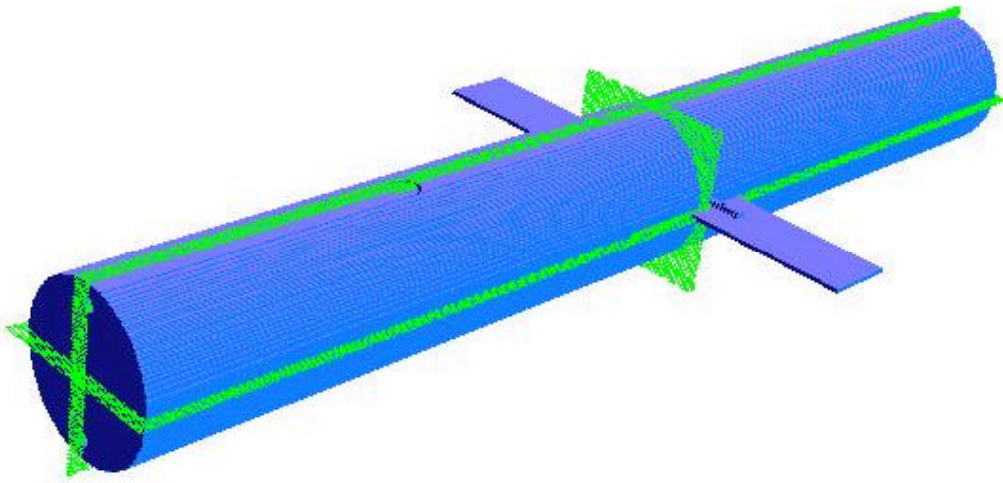
- Swedish-German project to study HPM (High Power Microwave) protection
- Extensive measurements and simulations have been made on a generic missile, GENECC
- Measurements are reported in detail in a companion paper by the same authors

Simulation Parameters

- Finite Difference Time Domain (FDTD) simulations with 1 mm spatial resolution
- 900 x 400 x 300 unit cells
- Illumination with Gaussian plane wave pulse
- Frequency range: 0 - 18 GHz
- Lossy dielectric parts with $\epsilon_r = 5.0 + j0.2$ and $\epsilon_r = 5.0 + j0.05$
- 4 layer PML absorbing boundary condition

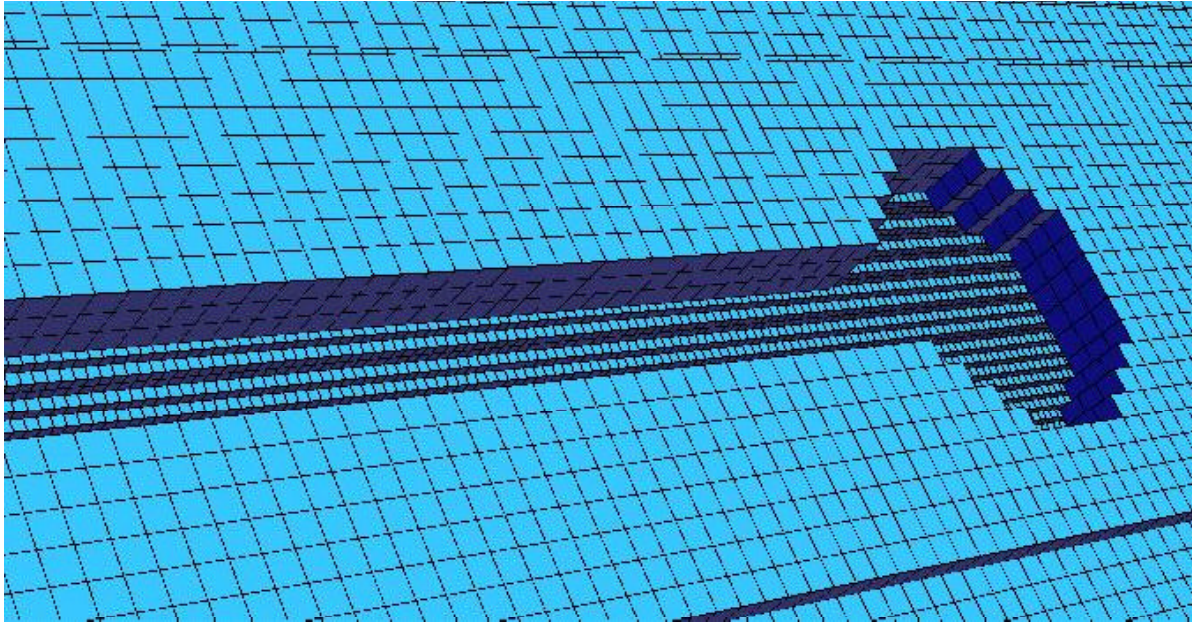
FDTD Model of GENECC

*External view with
three fictitious probe
planes in green*



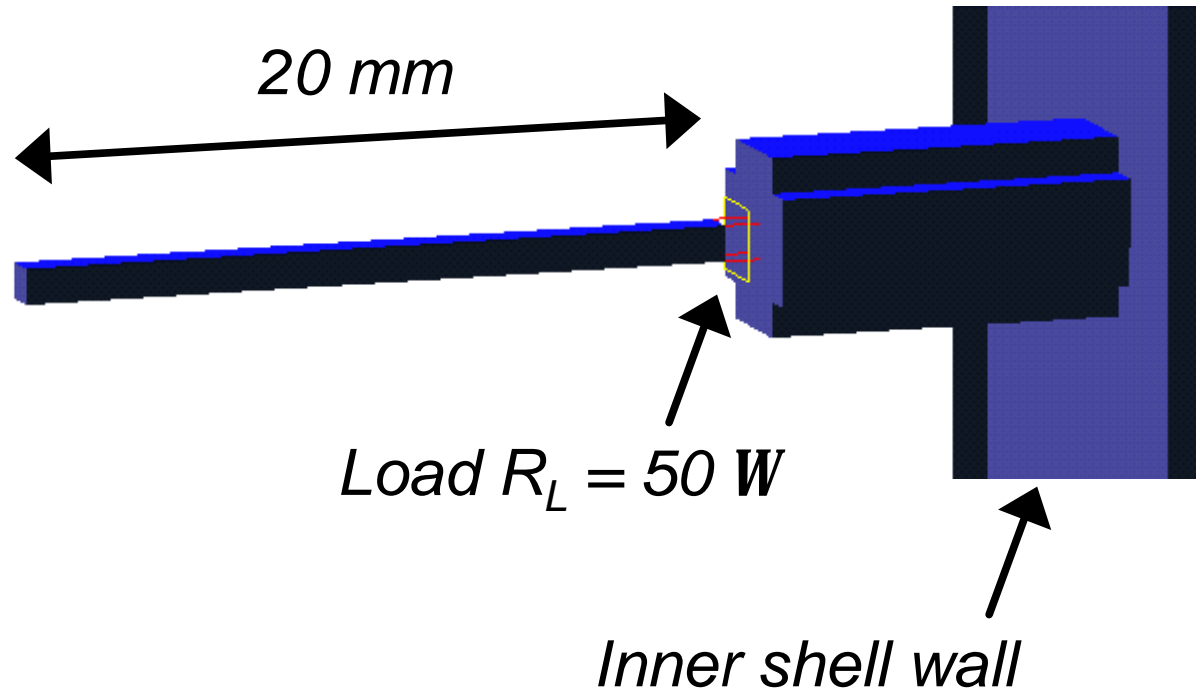
Internal structure

Slots



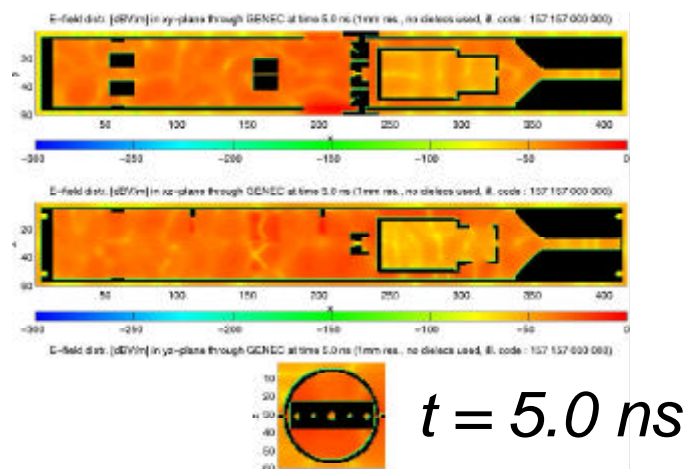
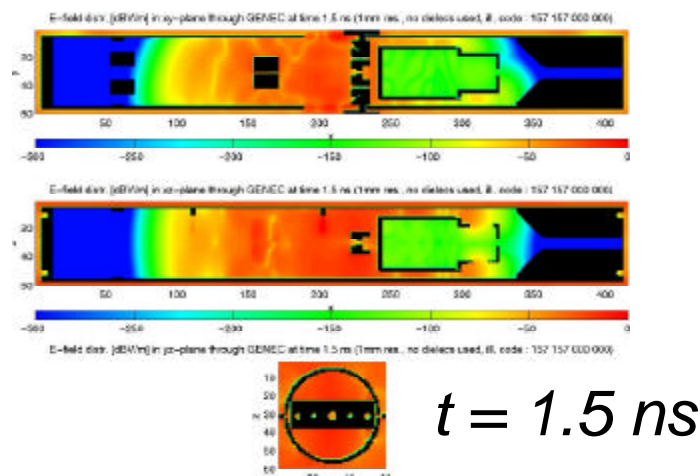
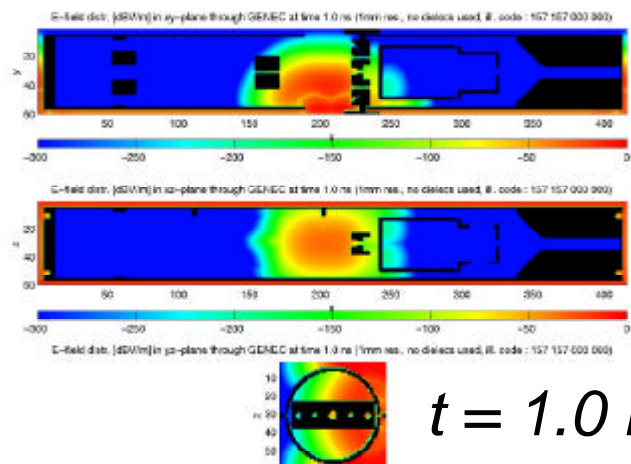
Close-up of one of the two slots at the wing suspension holes

Probes



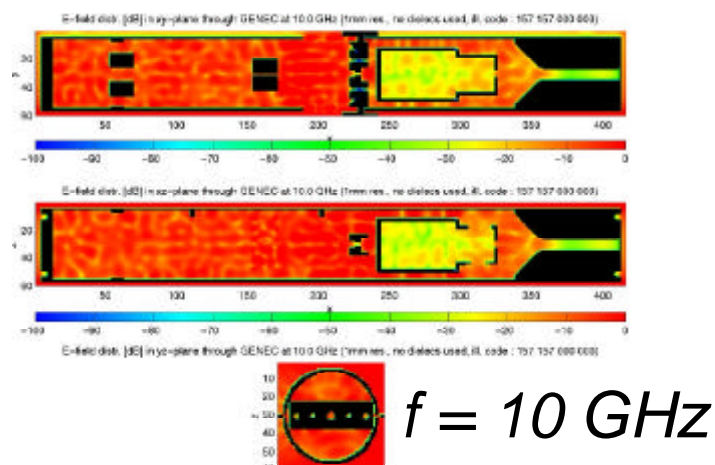
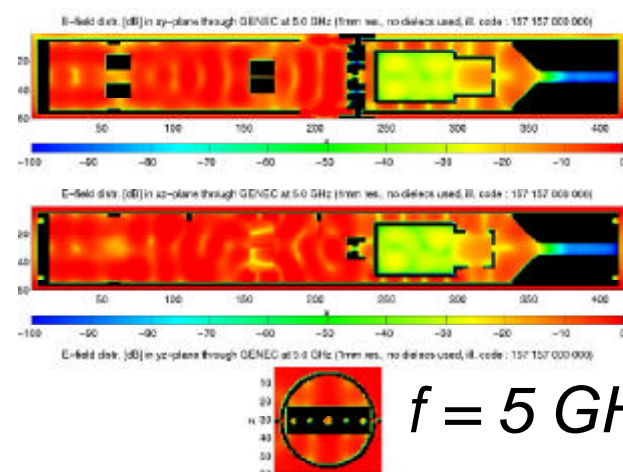
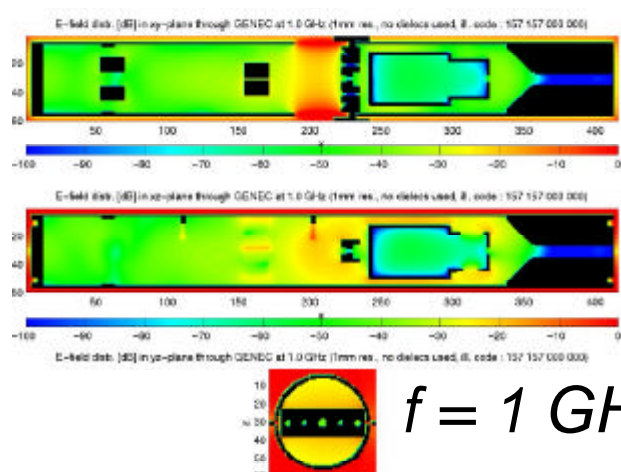
Close-up of one of the two probes

Field Patterns in Time Domain



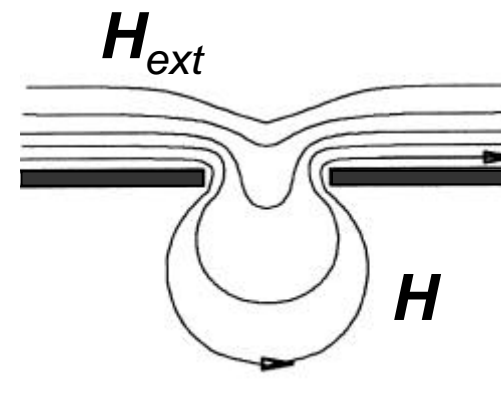
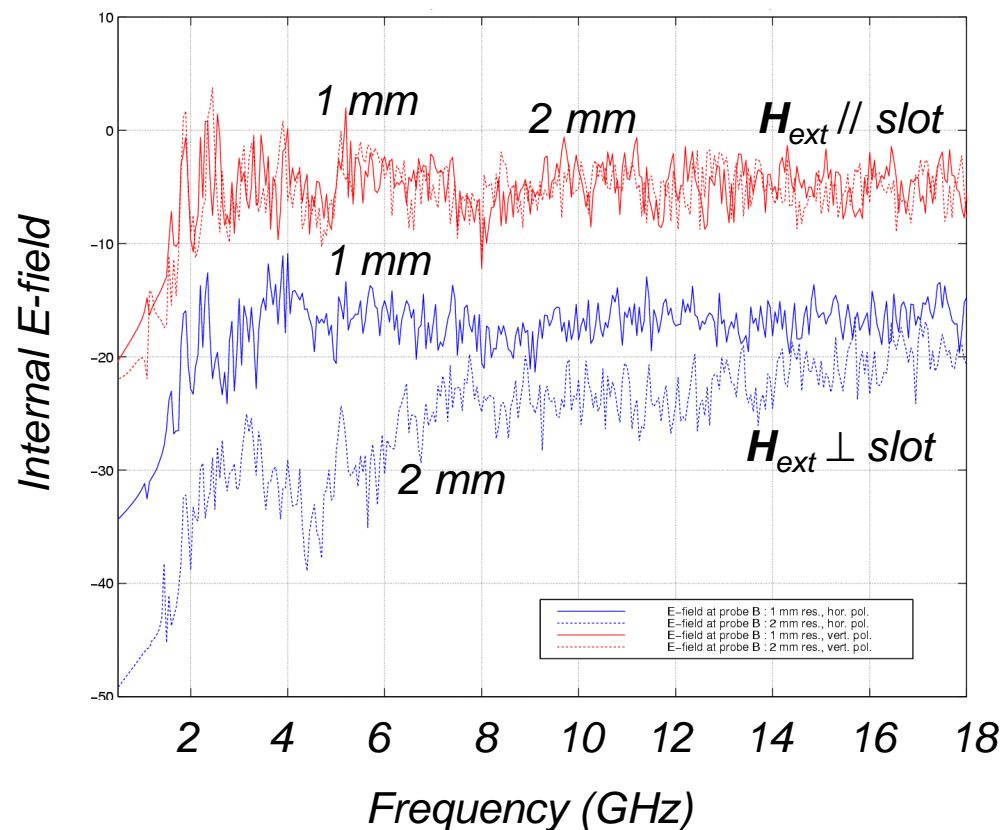
*Electric field amplitude
at three different times*

Field Patterns in Frequency Domain



Electric field amplitude at three different frequencies

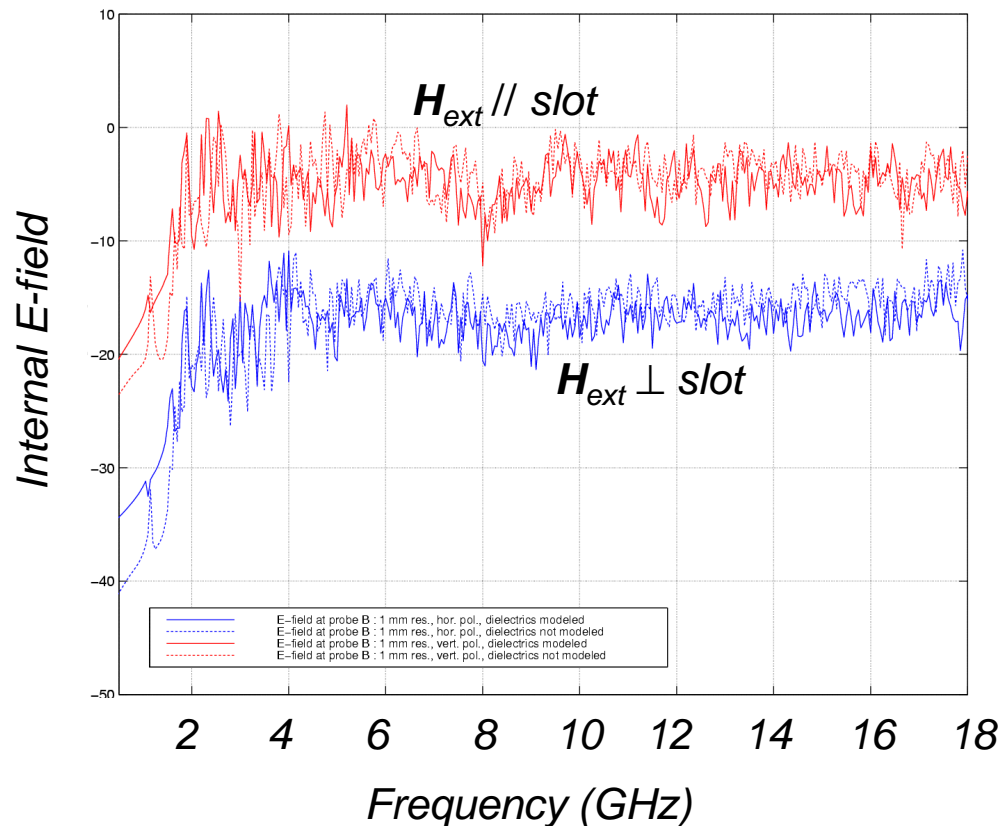
Impact of Spatial Resolution (1 mm vs. 2 mm)



$H_{ext} // \text{slot}$ (red): Many cells available to resolve H -line bending

$H_{ext} \perp \text{slot}$ (blue): Few cells available to resolve H -line bending

Effect of Internal Lossy Dielectric Structure



Internal losses have little effect on field level (solid: dielectrics included, dashed: no dielectrics)

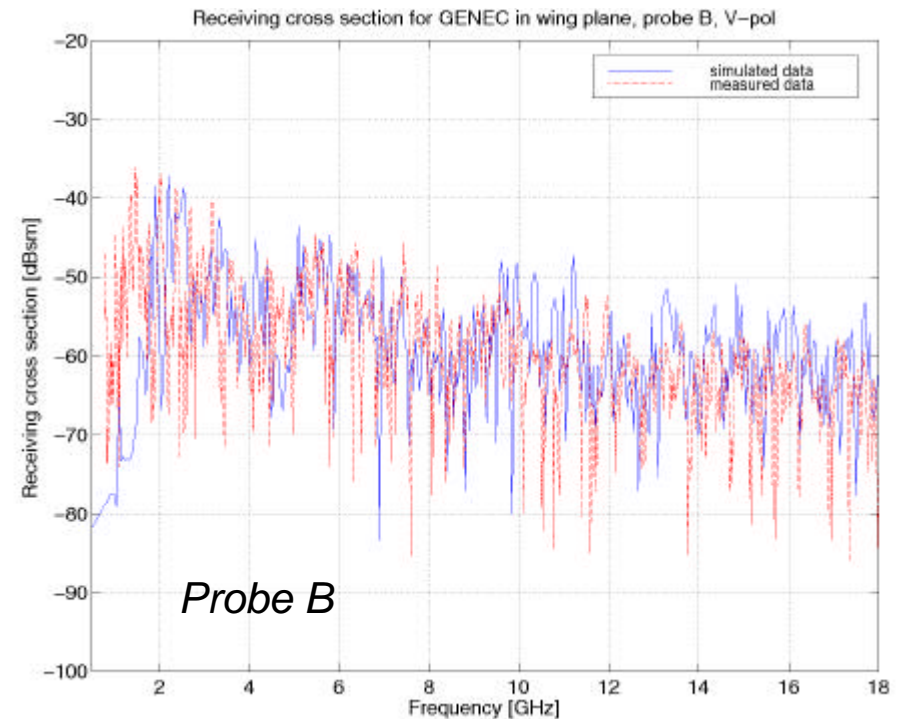
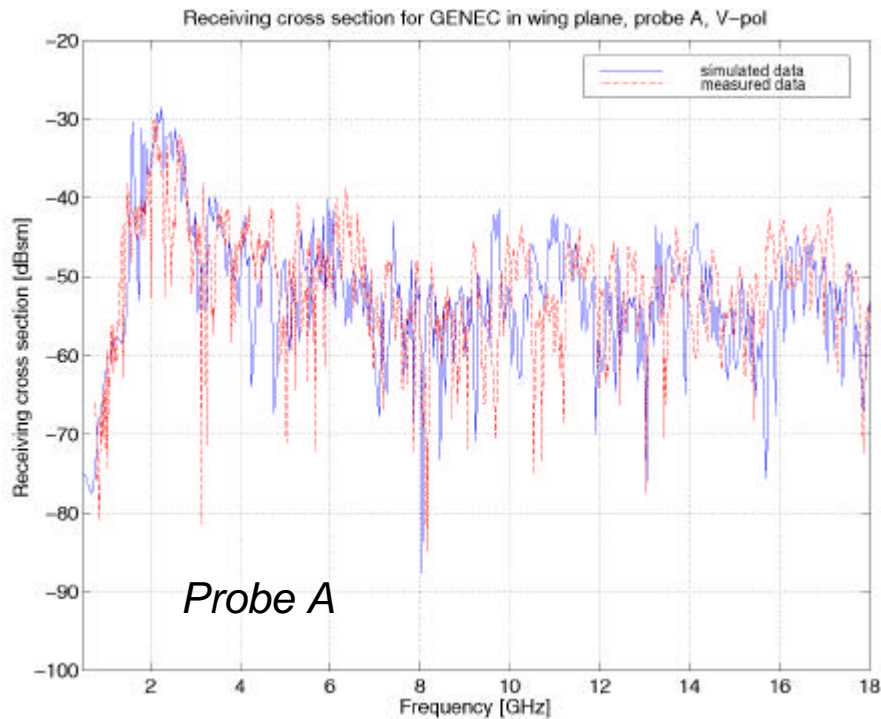
Losses through slots dominate for frequencies above slot cut-off (i.e. for $f > 1.9$ GHz)

Simulation vs. measurement

- Simulations compared with detailed measurements in anechoic chamber
- Power density S_{inc} in incident plane wave
- Relevant parameter for comparison is the receiving cross-section S_P , defined in terms of the power delivered by the probe

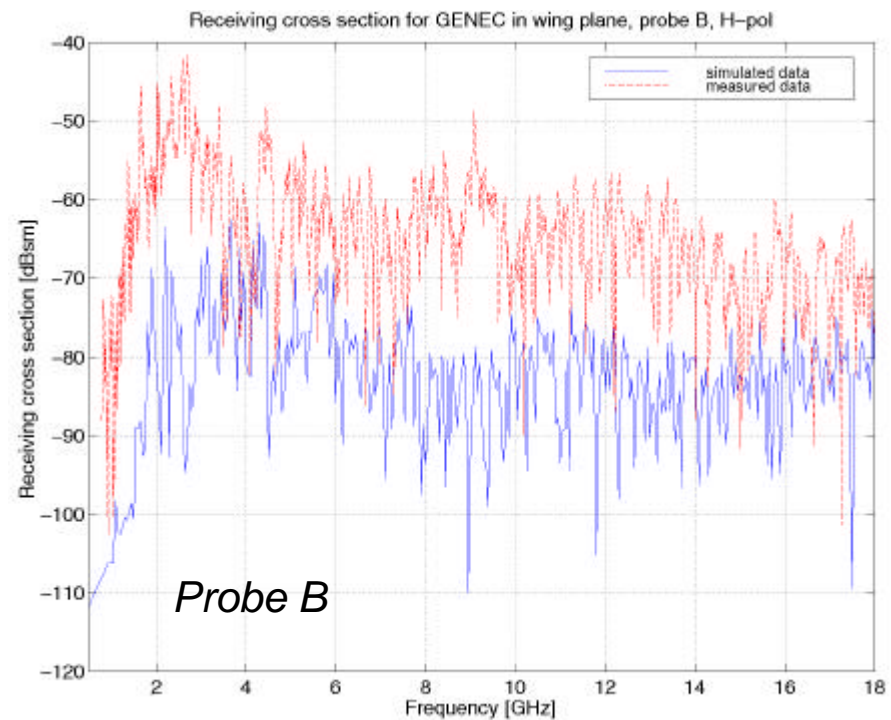
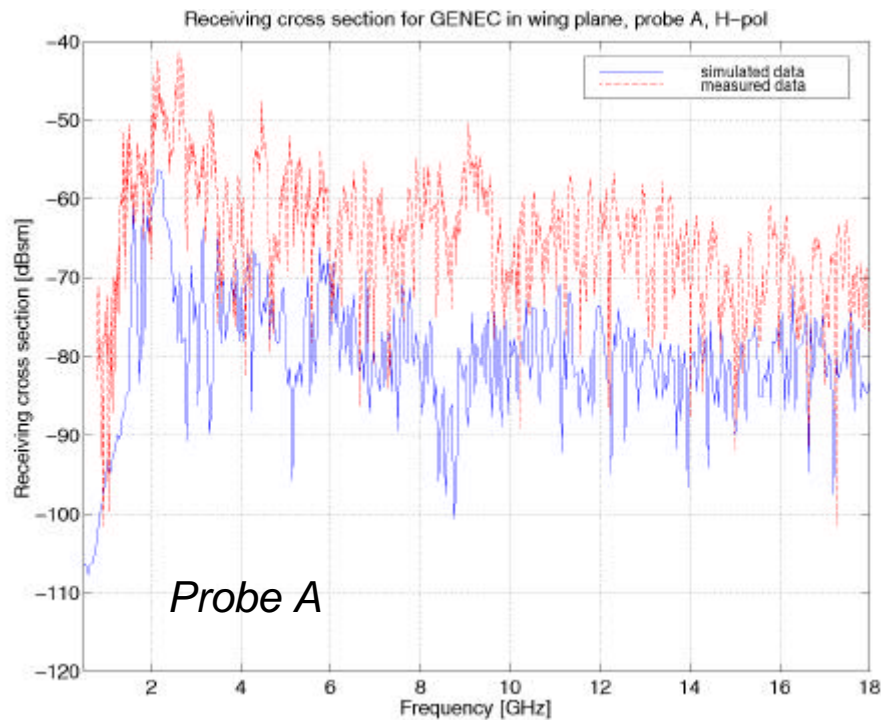
$$S_{P,meas} = \frac{P_{rec,probe}}{S_{inc}} \quad S_{P,sim} = \frac{R_L I_L^2}{S_{inc}}$$

Simulation vs. measurement ($H_{\text{ext}} // \text{slot}$)



Excellent agreement between simulated (blue) and measured (red) data

Simulation vs. measurement ($H_{\text{ext}} \perp \text{slot}$)



Deviations probably due to: (i) too few cells across the slot or (ii) other penetration channels in GENE

Conclusions (I)

- The worst, and most interesting, case ($H_{\text{ext}} // \text{slot}$) is accurately modeled
- Other cases with less leakage may require:
(i) finer resolution, (ii) subcell model, or (iii) some hybrid method
- Lossy dielectric structure has little influence for frequencies above slot cut-off

Conclusions (II)

- Agreement between measurements and simulations is indeed achievable, provided:
 1. Measurement setup is carefully defined and controlled
 2. Simulations have sufficient spatial resolution and correct material description

Conclusions (III)

- Uncertainties are to some degree present in measurements as well as in simulations
- “Correct” values of field levels are, however, usually defined *a priori* as measurement data obtained according to some standard
- Question: What accuracy is actually needed?
- Often, both methods may be used for comparative studies of different design solutions